

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re PATENT application of

Shunpei YAMAZAKI et al.

Serial No. 09/239,948

Filed: 01/29/99

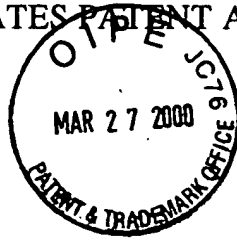
For: LASER PROCESSING METHOD, METHOD)

FOR FORMING A FLASH MEMORY, )

INSULATED GATE SEMICONDUCTOR )

DEVICE AND METHOD FOR FORMING )

THE SAME )



) Art Unit: 2811

) Examiner: G. Munson

CERTIFICATE OF MAILING

I hereby certify that this correspondence is being deposited with the United States Postal Service with sufficient postage as First Class Mail in an envelope addressed to: Assistant Commissioner for Patents, Washington, DC 20231 on \_\_\_\_\_.

\_\_\_\_\_  
Rose M. Fichtel

SUPPLEMENTAL AMENDMENT

Honorable Assistant Commissioner of Patents

Washington, D.C. 20231

Sir:

Please amend the above-identified application as follows:

In the specification:

Page 14, line 7, change "Hei-3-383981" to --Hei-3-283981--.

Page 17, lines 24-26, delete ", and the same process described in Japanese patent application No. Hei-3-278705 (filed September 30, 1991) can be followed)"


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REMARKS

The specification has been amended to remove reference to JP 3-278705, which appears to be a typographical error. The '705 application does not refer to anodic oxidation and this is deleted to avoid confusion in the specification. It may be that this should refer to JP 3-278704, which is the priority application of U.S. Patent 5,495,121 submitted herewith.

Examination on the merits is requested.

Respectfully submitted,

  
\_\_\_\_\_  
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